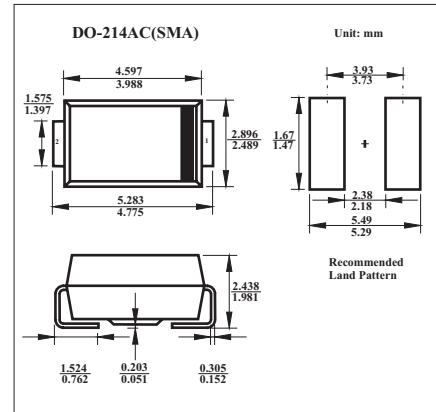


## Schottky Barrier Rectifier Diodes KL12 THRU KL14

### ■ Features

- For Surface Mounted Applications
- Metal Silicon Junction, Majority Carrier Conduction
- Low Power Loss, High Efficiency
- High Forward Surge Current Capability



### ■ Maximum Ratings and Electrical Characteristics @ Ta = 25°C

Parameter	Symbol	KL12	KL13	KL14	Unit
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	20	30	40	V
Maximum RMS voltage	V <sub>RMS</sub>	14	21	28	
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	
Maximum Average Forward Rectified Current	I(AV)	1.0			A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	30			A
Maximum Instantaneous Forward Voltage at 1.0A	V <sub>F</sub>	0.38	0.38	0.40	V
Maximum DC Reverse Current TA=25°C	I <sub>R</sub>	0.5			mA
At Rated DC Blocking Voltage TA=100°C		20			
Typical Thermal Resistance *	R <sub>θJA</sub>	88.0			°C/W
	R <sub>θJL</sub>	28			
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +125			°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150			°C

\* P.C.B mounted with 0.2X0.2"(5.0x5.0mm)copper pad areas